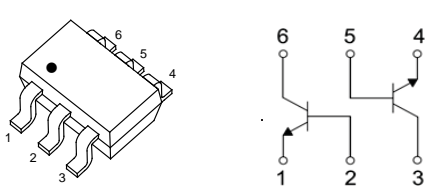


DUAL TRANSISTOR (NPN+NPN)	SOT-363 Plastic-Encapsulate Transistors
<p style="text-align: center;"><u>SOT-363</u></p> 	<h3>Features</h3> <ul style="list-style-type: none"> <li>• Epitaxial Planar Die Construction</li> <li>• Complementary PNP Type Available(MMDT5401)</li> <li>• Ideal for Medium Power Amplification and Switching</li> </ul>

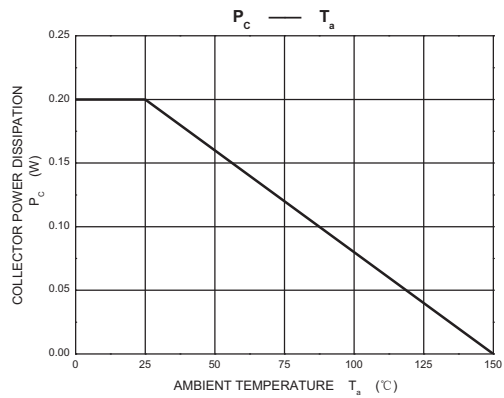
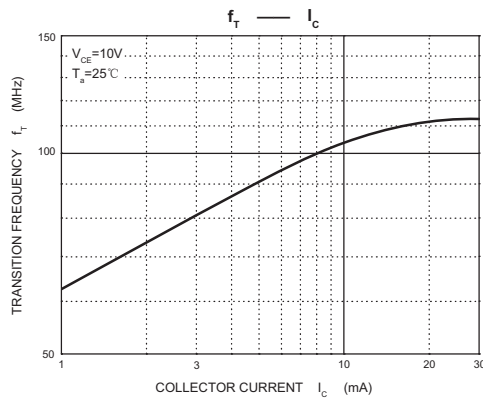
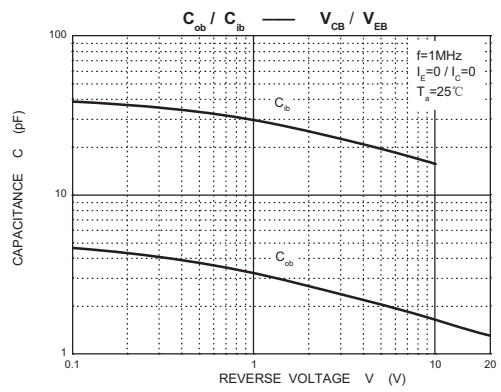
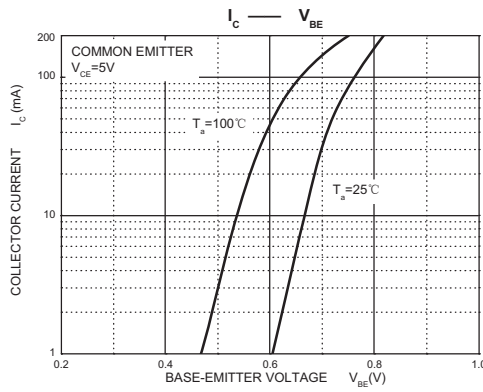
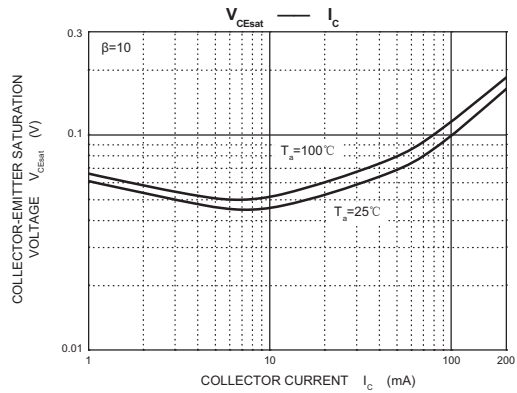
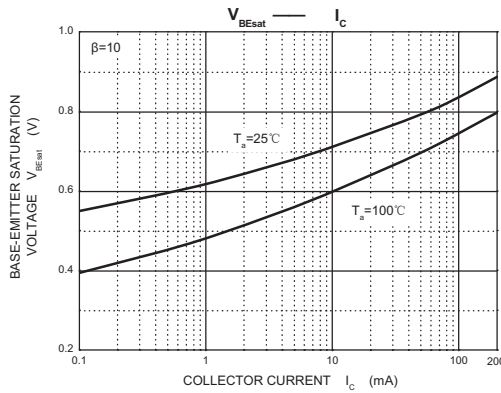
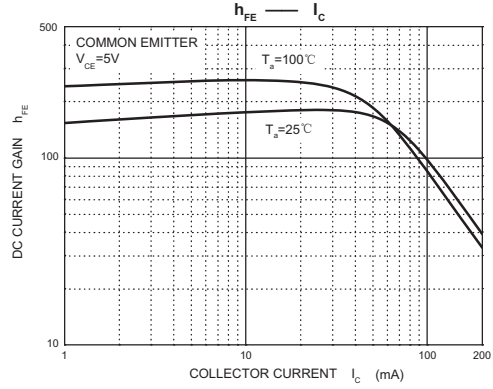
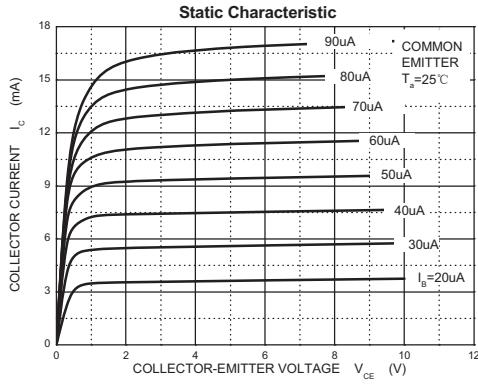
### MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector- Base Voltage	180	V
V <sub>CEO</sub>	Collector-Emitter Voltage	160	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current -Continuous	0.2	A
P <sub>C</sub>	Collector Power Dissipation	0.2	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C

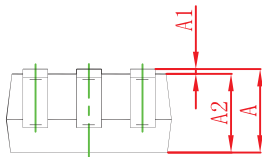
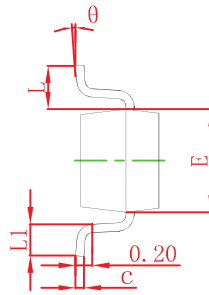
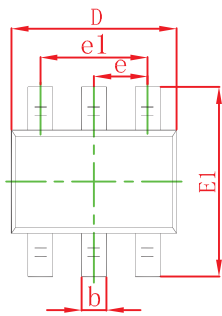
### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =100μA, I <sub>E</sub> =0	180			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	160			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =10μA, I <sub>C</sub> =0	6			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =120V, I <sub>E</sub> =0			0.05	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =4V, I <sub>C</sub> =0			0.05	μA
	h <sub>FE(1)</sub>	V <sub>CE</sub> =5 V, I <sub>C</sub> =1mA	80			
	h <sub>FE(2)</sub>	V <sub>CE</sub> =5 V, I <sub>C</sub> =10mA	100		300	
	h <sub>FE(3)</sub>	V <sub>CE</sub> =5 V, I <sub>C</sub> =50mA	30			
Collector-emitter saturation voltage	V <sub>CE(sat)1</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA			0.15	V
	V <sub>CE(sat)2</sub>	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA			0.2	V
Base-emitter saturation voltage	V <sub>BE(sat)1</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA			1	V
	V <sub>BE(sat)2</sub>	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA			1	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA, f=100MHz	100		300	MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz			6	pF
Noise Figure	NF	V <sub>CE</sub> =5V, I <sub>C</sub> =0.2mA, R <sub>S</sub> =1KΩ, f=1kHz			8	dB

**Typical Characteristics**

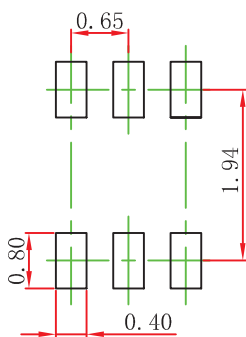


**SOT-363 Package Outline Dimensions**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.400	0.085	0.094
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
theta	0°	8°	0°	8°

**SOT-363 Suggested Pad Layout**



- Note:
1. Controlling dimension: in millimeters.
  2. General tolerance:  $\pm 0.05\text{mm}$ .
  3. The pad layout is for reference purposes only.

单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)